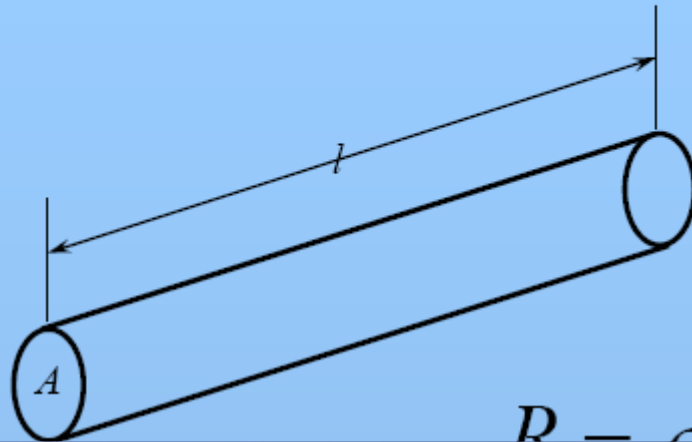


# Electrical Conduction Theories & Conducting Materials (Part-A)

## Outline:

- \* Resistivity, TCR, and Matthiessen's rule
- \* Classification of metals, insulators, and semiconductors
- \* Free electron theory
- \* Hall effect
- \* Nordheim's rule

## Resistivity & Temperature coefficient of resistivity (TCR)



$$R = \rho \times \frac{l}{A}$$

Electrical resistance ( $\Omega$ )

Electrical resistivity ( $\Omega \cdot \text{m}$ )

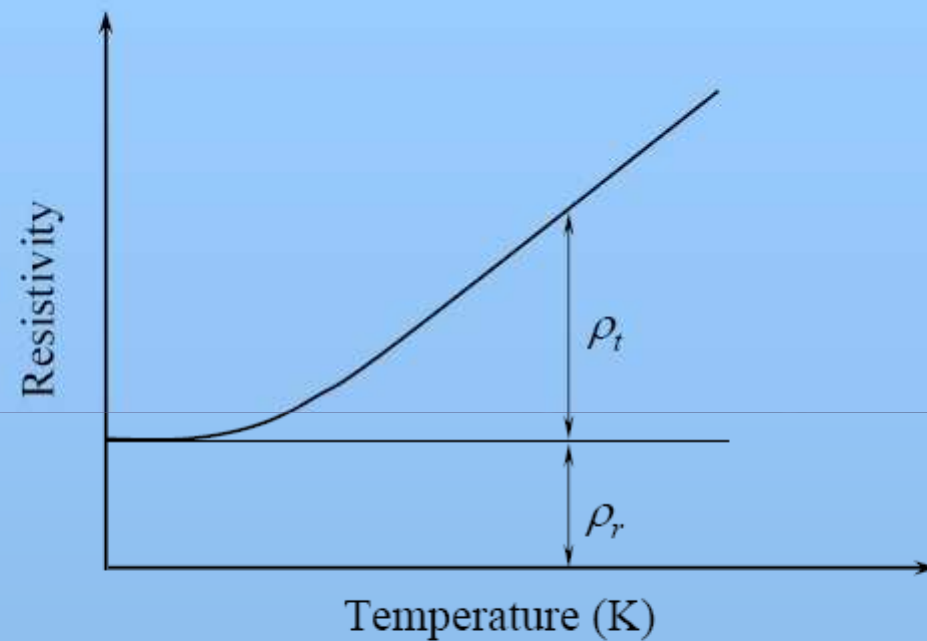
Length (m)

Area of the cross-section of the conductor ( $\text{m}^2$ )

$$\sigma = \frac{1}{\rho}$$

Conductivity ( $\Omega^{-1} \text{m}^{-1}$ )

## Matthiessen's rule and TCR



**Matthiessen's rule:** the resistivity  $\rho$  of a pure metal is the sum of a residual part  $\rho_r$  and a thermal part  $\rho_t$ .

$$\rho_{(total)} = \rho_r + \rho_t$$

## Matthiessen's rule and TCR

$$\rho_{(total)} = \rho_r + \rho_t$$

$$\rho_{(total)} = \rho_r \left( 1 + \frac{\rho_t}{\rho_r} \right)$$

$$\frac{\rho_t}{\rho_r} = f(T)$$

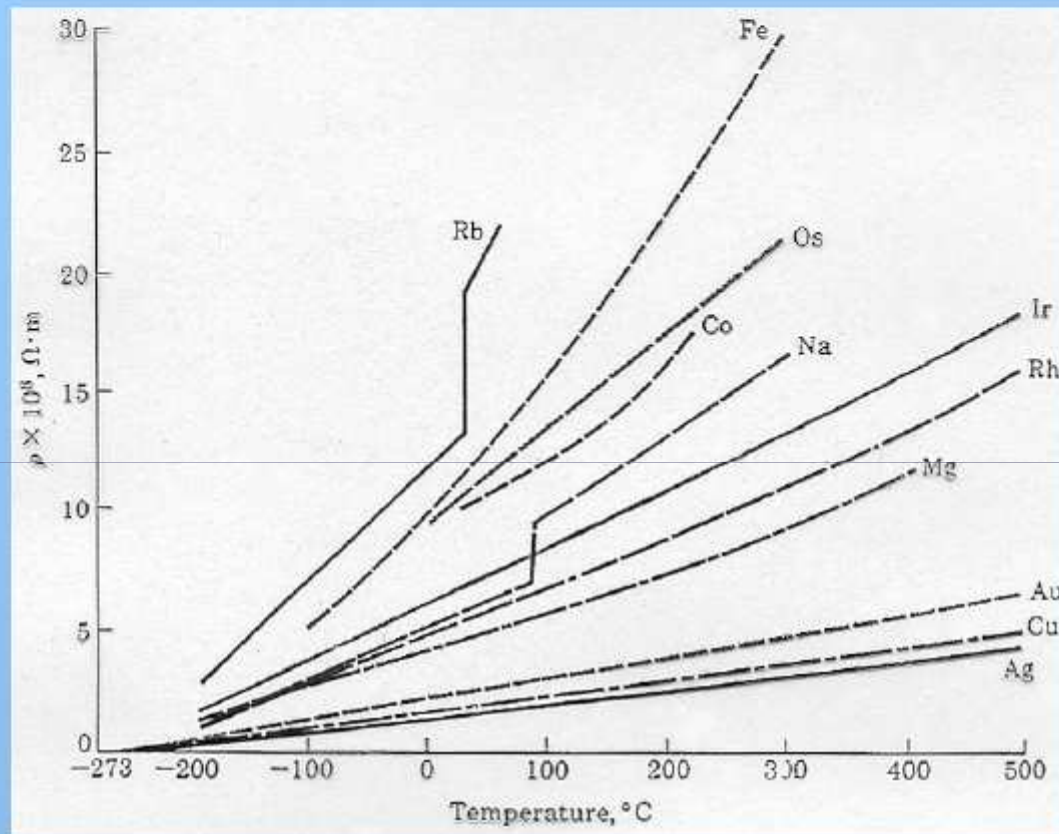
$$\rho_{(total)} = \rho_r [1 + f(T)]$$

For most metals and alloys,  $\rho$  is approximately proportional to temperature  $T$ ,

$$\rho_{(total)} = \rho_o (1 + \alpha \Delta T)$$



Temperature coefficient of resistivity (TCR)



Effect of temperature on resistivity of selected metals

Table 2.1 Resistivities and TCRs at 293 K

	Material	$\rho$ ( $\Omega m$ )	TCR (%/K)
Conducting materials	Silver	$1.6 \times 10^{-8}$	+ 0.41
	Copper	$1.7 \times 10^{-8}$	+ 0.43
	Aluminium	$2.7 \times 10^{-8}$	+ 0.43
Heating elements	Sodium	$5.0 \times 10^{-8}$	+ 0.4
	Tungsten	$5.7 \times 10^{-8}$	+ 0.45
	Iron	$9.7 \times 10^{-8}$	+ 0.5
	Platinum	$10.5 \times 10^{-8}$	+ 0.39
	Tantalum	$13.5 \times 10^{-8}$	+ 0.38
	Manganin (87Cu13Mn)	$38 \times 10^{-8}$	+ 0.001
	Constantan (57Cu43Ni)	$49 \times 10^{-8}$	+ 0.002
	Nichrome (80Ni20Cr)	$112 \times 10^{-8}$	+ 0.0085
	SiC, commercial	$1-2 \times 10^{-6}$	- 0.15
	Graphite, commercial	c. $1 \times 10^{-5}$	- 0.07
Semi-conductors	InAs, very pure	$3 \times 10^{-3}$	- 1.7
	Tellurium, very pure	$4 \times 10^{-3}$	- 2
	Germanium, diode grade	$1 \times 10^{-3}$	+ 0.4
	Germanium, very pure	$5 \times 10^{-1}$	- 4
	Silicon, transistor grade	$1 \times 10^{-1}$	+ 0.8
	Silicon, very pure	$1 \times 10^{-3}$	- 7
	Anthracene	3	- 10
Insulators	Selenium, amorphous	c. $1 \times 10^{10}$	- 15
	Silica	c. $1 \times 10^{13}$	negative
	Alumina	c. $1 \times 10^{14}$	negative
	Sulphur	c. $1 \times 10^{15}$	negative
	PTFE	c. $1 \times 10^{16}$	negative

Conductivity



Drude's free electron theory (1900)

Electrons, treated as particles with certain mass and electric charge, move through the metal lattice freely and obey Newton's laws of motion and Maxwell-Boltzmann statistics



Paul Drude (1863-1906)

## Drude's free electron theory

when an electric field  $E$  is applied to a metal, the force acting on an electron is:

$$F = -eE$$

According to the 2<sup>nd</sup> Newton's Law:

$$a = F/m = -eE/m = 1.75 \times 10^{11} E$$

Acceleration      Mass of an electron,  $9.1 \times 10^{-31} \text{kg}$

In a time  $\tau$ , the velocity  $v_d$  of the electron will be:

$$v_d = a\tau$$

Drift velocity





$$v_d = -eE\tau / m$$

$$\mu = e\tau / m$$

Mobility of electron, or drift velocity in unit electrical field

Considering a unit volume of a conductor containing  $n$  free electron, the charge crossing unit area in unit time must be  $-nev_d$ , which is the **current density**  $J$ :

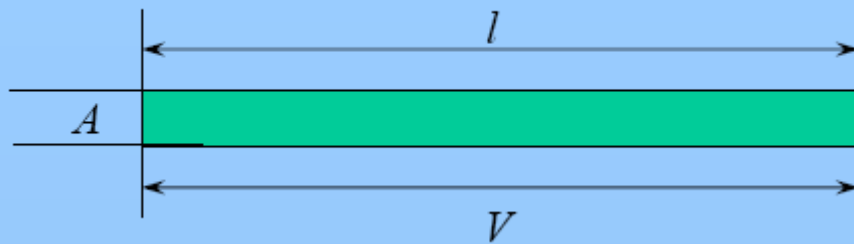
$$J = -nev_d = ne^2 E \tau / m$$

or

$$J = \sigma E$$

$$\sigma = ne^2 \tau / m = ne\mu$$

Conductivity of a metal, proportional to mobility and free electron density



$$E = \frac{V}{l}$$

$$R = \rho \times \frac{l}{A}$$

Since

$$J = \sigma E = \frac{E}{\rho} = \frac{V}{\rho l}$$

We get

$$J = \frac{V}{RA}$$

$$JA = I = \frac{V}{R} \longrightarrow \text{Ohm's law}$$

## Mean free path

The average distance travelled by an electron between collisions:

$$l_m = \tau v$$

Time between two collisions      Average velocity of electron,  $v = v_{th} + v_d$

Since:

$$v_{th} \phi \phi v_d$$
$$\tau = \mu m / e$$

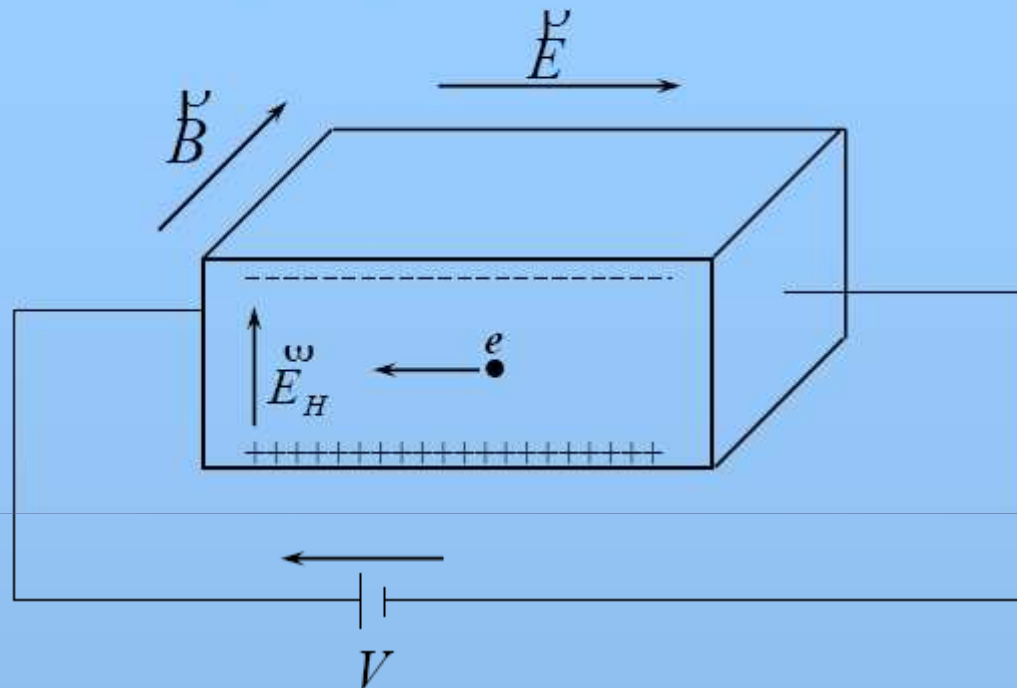
We get:

$$l_m = \mu m v_{th} / e$$

Typically,  $\tau = 10^{-14} \sim 10^{-15}$  Sec, electron concentration =  $10^{28}/\text{m}^3$ , therefore:

$$\sigma = ne^2 \tau / m = 0.3 - 3 \times 10^6 / (\Omega \cdot m)$$

## Hall effect (1879)



Edwin Hall (1855-1938)

Electrons moving in a magnetic field are subjected to the **Lorenz force**,  $F$ :

$$F = -ey \times B$$

Instantaneous velocity of electron

Magnetic induction

The electrons move upwards to accumulate and produce a field,  $E_H$ , **Hall field**, which acts on the electrons as to oppose the Lorenz force;

$$eE_H = evB$$

Since:

$$v = v_{th} + v_d$$

$$v_{th} \approx 0 \quad \longrightarrow \quad E_H = v_d B$$

We get:

$$E_H = \mu EB$$

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Also, since:

$$v_d = -J / ne$$

We then have:

$$E_H = \left( -\frac{1}{ne} \right) JB$$

$\longleftarrow$   $R_H$ , Hall constant

$$R_H = \frac{E_H}{JB}$$

$R_{Hne}$  values for some metals

<b>Metal</b>	<b><math>R_{Hne}</math></b>
Li	-1.15
Na	-1.05
K	-1.08
Rb	-1.05
Cs	-1.04
Cu	-0.68
Ag	-0.8
Au	-0.69
Pd	-0.73
Pt	-0.21
Cd	+0.5
W	+1.2
Be	+5.0

## Resistivity of alloys

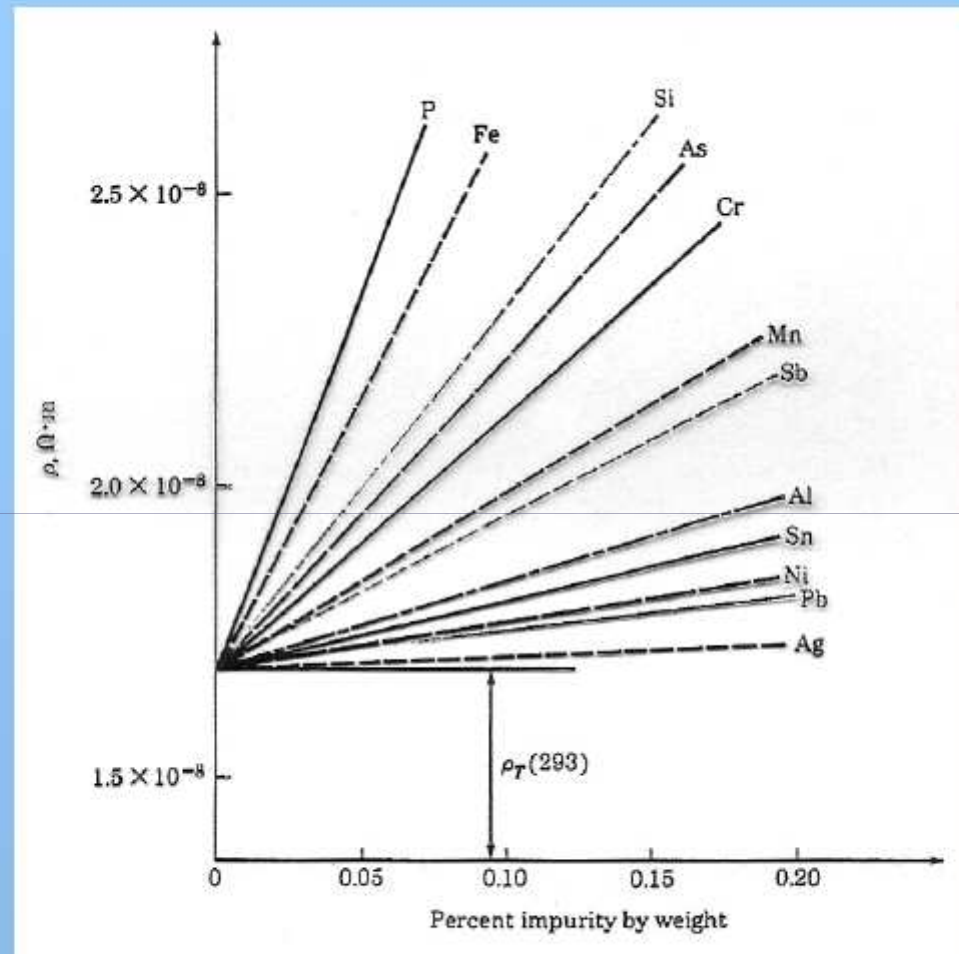
Impurity increases the residual part  $\rho_r$  of  $\rho_{(total)}$ .

$$\rho_r(x) = Ax(1-x) \quad \text{Nordheim's rule}$$

Solution resistivity coefficient    Concentration of the impurity

When  $x \ll 1$ ,  $1 - x \approx 1$ , then we have:

$$\rho_r = Ax$$



Effects of small additions of various elements on the resistivity of Cu at 293K



### Example: Calculation of Mobility and Drift Velocity

Cu is the most important conducting metal. There is one valence electron per Cu atom. Cu has a *fcc* crystal structure with 4 atoms in a unit cell, a lattice parameter of 0.360 nm, and resistivity of  $1.7 \times 10^{-8} \Omega\text{m}$ .

*Assuming valence electron = free electron*

- (1) Calculate the mobility of electron in Cu.
- (2) A typical house wire 3 m long has a resistance  $R = 0.03 \Omega$  and carries a current of 15 A. Calculate the drift velocity of an electron in the wire.
- (3) Calculate the time  $\tau$  between two collisions of electron.
- (4) Assuming the thermal velocity of an electron is  $\sim 10^5$  m/s, calculate the mean free path of an electron in Cu wire.

1.  $\mu = \sigma / (n e) = 1 / (\rho n e)$

2.  $v_d = \mu E$

3.  $v_d = -e E \tau / m$

4.  $l_m = \tau v_{th}$